



TN12, TS12 and TYNx12 Series

SENSITIVE & STANDARD

12A SCRs

Table 1: Main Features

| Symbol | Value | Unit |
|-------------------|-------------|------|
| $I_{T(RMS)}$ | 12 | A |
| V_{DRM}/V_{RRM} | 600 to 1000 | V |
| I_{GT} | 0.2 to 15 | mA |

DESCRIPTION

Available either in sensitive (**TS12**) or standard (**TN12 / TYN**) gate triggering levels, the 12A SCR series is suitable to fit all modes of control, found in applications such as overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition and voltage regulation circuits...

Available in through-hole or surface-mount packages, they provide an optimized performance in a limited space area.

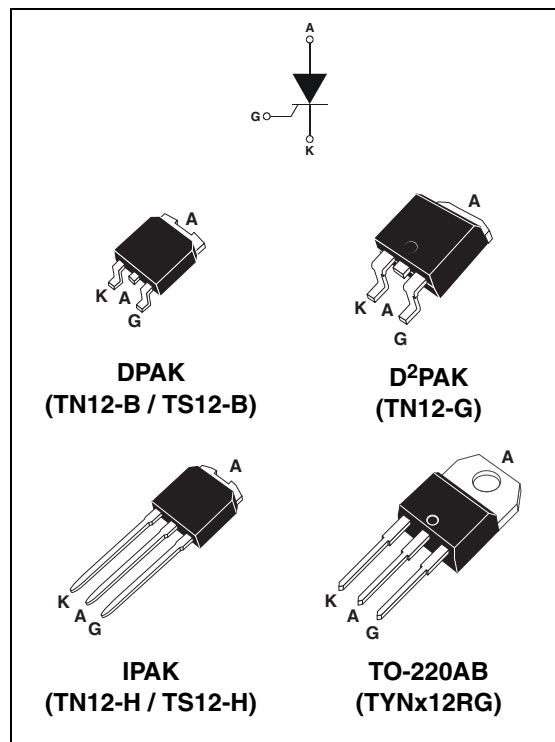


Table 2: Order Codes

| Part Numbers | Marking |
|----------------|------------|
| TN1215-x00B | TN1215x00 |
| TN1215-x00B-TR | TN1215x00 |
| TN1215-x00G | TN1215x00G |
| TN1215-x00G-TR | TN1215x00G |
| TN1215-x00H | TN1215x00 |
| TS1220-x00B | TS1220x00 |
| TS1220-x00B-TR | TS1220x00 |
| TS1220-x00H | TS1220x00 |
| TYNx12RG | TYNx12 |
| TYNx12TRG | TYNx12T |

TN12, TS12 and TYNx12 Series

Table 3: Absolute Ratings (limiting values)

| Symbol | Parameter | | Value | | Unit | |
|--------------------|---|------------------------|---------------------------|--------------------------------|------|------------------------|
| | | | TN12-G TYN12 | TN12-B/H TS12-B/H | | |
| $I_{T(RMS)}$ | RMS on-state current (180° conduction angle) | | $T_c = 105^\circ\text{C}$ | 12 | A | |
| $I_{T(AV)}$ | Average on-state current (180° conduction angle) | | $T_c = 105^\circ\text{C}$ | 8 | A | |
| I_{TSM} | Non repetitive surge peak on-state current | $t_p = 8.3 \text{ ms}$ | $T_j = 25^\circ\text{C}$ | 145 | 115 | A |
| | | $t_p = 10 \text{ ms}$ | | 140 | 110 | |
| I^2t | I^2t Value for fusing | $t_p = 10 \text{ ms}$ | $T_j = 25^\circ\text{C}$ | 98 | 60 | A^2s |
| di/dt | Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100 \text{ ns}$ | $F = 60 \text{ Hz}$ | $T_j = 125^\circ\text{C}$ | 50 | | $\text{A}/\mu\text{s}$ |
| I_{GM} | Peak gate current | $t_p = 20 \mu\text{s}$ | $T_j = 125^\circ\text{C}$ | 4 | | A |
| $P_{G(AV)}$ | Average gate power dissipation | | $T_j = 125^\circ\text{C}$ | 1 | | W |
| T_{stg} T_j | Storage junction temperature range Operating junction temperature range | | | - 40 to + 150 - 40 to + 125 | | $^\circ\text{C}$ |
| V_{RGM} | Maximum peak reverse gate voltage (for TN12 & TYN12 only) | | | 5 | | V |

Tables 4: Electrical Characteristics ($T_j = 25^\circ\text{C}$, unless otherwise specified)

■ SENSITIVE

| Symbol | Test Conditions | | | TS1220 | Unit | |
|------------------------|--|---------------------------|---------------------------|--------|------------------------|------------------|
| I_{GT} | $V_D = 12 \text{ V}$ $R_L = 140 \Omega$ | | MAX. | 200 | μA | |
| V_{GT} | | | MAX. | 0.8 | V | |
| V_{GD} | $V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $R_{GK} = 1 \text{ k}\Omega$ | $T_j = 125^\circ\text{C}$ | MIN. | 0.1 | V | |
| V_{RG} | $I_{RG} = 10 \mu\text{A}$ | | MIN. | 8 | V | |
| I_H | $I_T = 50 \text{ mA}$ $R_{GK} = 1 \text{ k}\Omega$ | | MAX. | 5 | mA | |
| I_L | $I_G = 1 \text{ mA}$ $R_{GK} = 1 \text{ k}\Omega$ | | MAX. | 6 | mA | |
| dV/dt | $V_D = 65 \% V_{DRM}$ $R_{GK} = 220 \Omega$ | $T_j = 125^\circ\text{C}$ | MIN. | 5 | $\text{V}/\mu\text{s}$ | |
| V_{TM} | $I_{TM} = 24 \text{ A}$ $t_p = 380 \mu\text{s}$ | | $T_j = 25^\circ\text{C}$ | MAX. | 1.6 | V |
| V_{t0} | Threshold voltage | | $T_j = 125^\circ\text{C}$ | MAX. | 0.85 | V |
| R_d | Dynamic resistance | | $T_j = 125^\circ\text{C}$ | MAX. | 30 | $\text{m}\Omega$ |
| I_{DRM} I_{RRM} | $V_{DRM} = V_{RRM}$ $R_{GK} = 220 \Omega$ | | $T_j = 25^\circ\text{C}$ | MAX. | 5 | μA |
| | | | $T_j = 125^\circ\text{C}$ | | 2 | mA |

■ STANDARD

| Symbol | Test Conditions | TN1215 | | TYN | | Unit | |
|------------------------|--|---------------------------|------|------|-----|------------------|----|
| | | B / H | G | x12T | x12 | | |
| I_{GT} | $V_D = 12\text{ V}$ $R_L = 33\ \Omega$ | MIN. | 2 | 0.5 | 2 | mA | |
| | | MAX. | 15 | 5 | 15 | | |
| V_{GT} | | MAX. | 1.3 | | | V | |
| V_{GD} | $V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_J = 125^\circ\text{C}$ | MIN. | 0.2 | | | V | |
| I_H | $I_T = 500\text{ mA}$ Gate open | MAX. | 40 | 30 | 15 | 30 | mA |
| I_L | $I_G = 1.2\ I_{GT}$ | MAX. | 80 | 60 | 30 | 60 | mA |
| dV/dt | $V_D = 67\% V_{DRM}$ Gate open $T_J = 125^\circ\text{C}$ | MIN. | 200 | 40 | 200 | V/ μs | |
| V_{TM} | $I_{TM} = 24\text{ A}$ $t_p = 380\ \mu\text{s}$ $T_J = 25^\circ\text{C}$ | MAX. | 1.6 | | | V | |
| V_{t0} | Threshold voltage $T_J = 125^\circ\text{C}$ | MAX. | 0.85 | | | V | |
| R_d | Dynamic resistance $T_J = 125^\circ\text{C}$ | MAX. | 30 | | | m Ω | |
| I_{DRM} I_{RRM} | $V_{DRM} = V_{RRM}$ | $T_J = 25^\circ\text{C}$ | 5 | | | μA | |
| | | $T_J = 125^\circ\text{C}$ | 2 | | | mA | |

Table 6: Thermal resistance

| Symbol | Parameter | Value | Unit | |
|---------------|--------------------------|--|--------------------|--------------------|
| $R_{th(j-c)}$ | Junction to case (DC) | 1.3 | $^\circ\text{C/W}$ | |
| $R_{th(j-a)}$ | Junction to ambient (DC) | S = 0.5 cm ² DPAK | 70 | $^\circ\text{C/W}$ |
| | | S = 1 cm ² D ² PAK | 45 | |
| | | IPAK | 100 | |
| | | TO-220AB | 60 | |

S = Copper surface under tab.

Figure 1: Maximum average power dissipation versus average on-state current

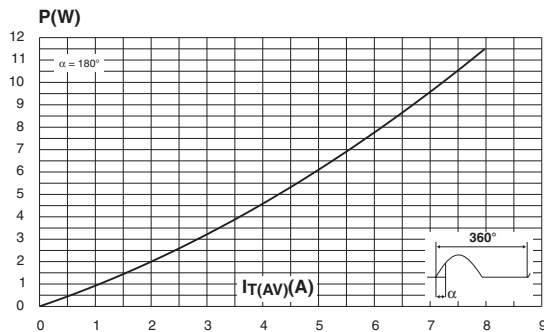


Figure 2: Average and D.C. on-state current versus case temperature

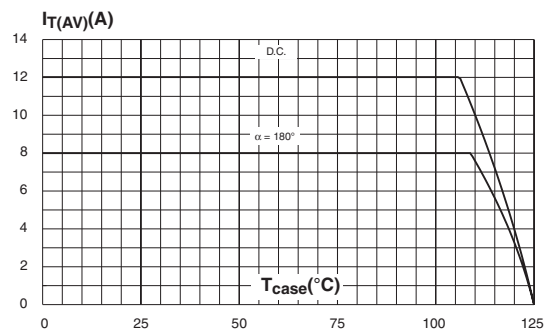


Figure 3: Average and D.C. on-state current versus ambient temperature (device mounted on FR4 with recommended pad layout) (DPAK)

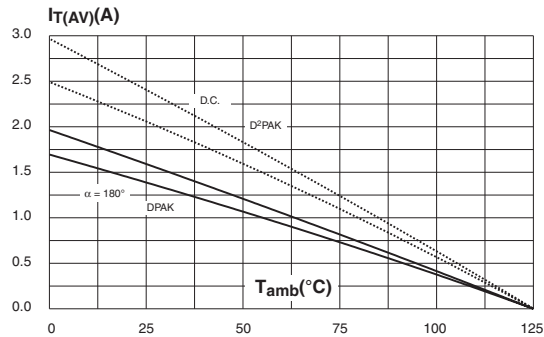


Figure 4: Relative variation of thermal impedance junction to case versus pulse duration

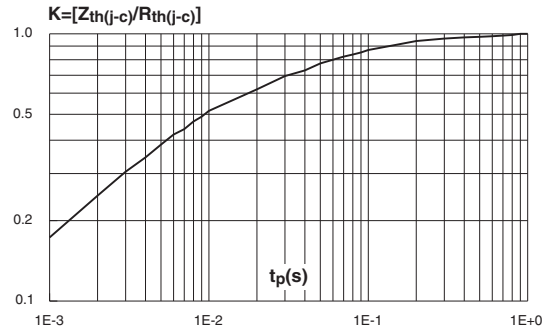


Figure 5: Relative variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, FR4 PC board for DPAK)

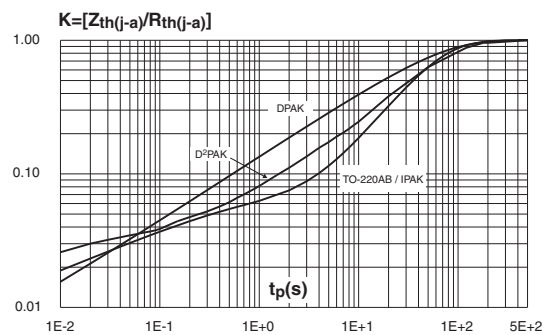


Figure 6: Relative variation of gate trigger current and holding current versus junction temperature for TS8 series

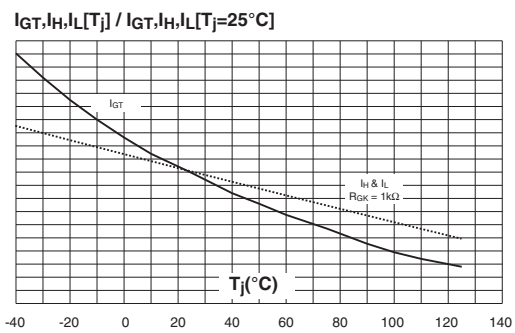


Figure 7: Relative variation of gate trigger current and holding current versus junction temperature for TN8 & TYN08 series

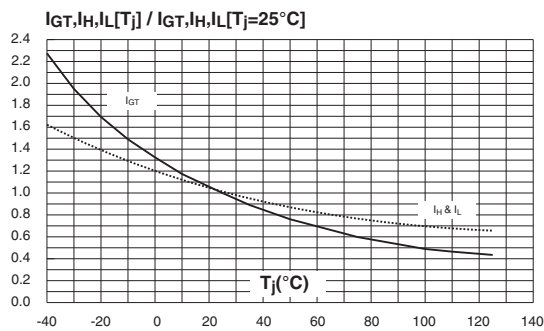


Figure 8: Relative variation of holding current versus gate-cathode resistance (typical values) for TS8 series

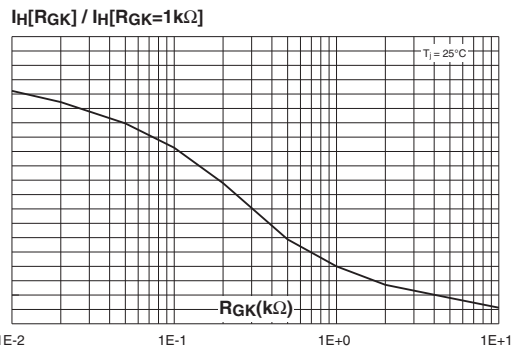


Figure 9: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values) for TS8 series

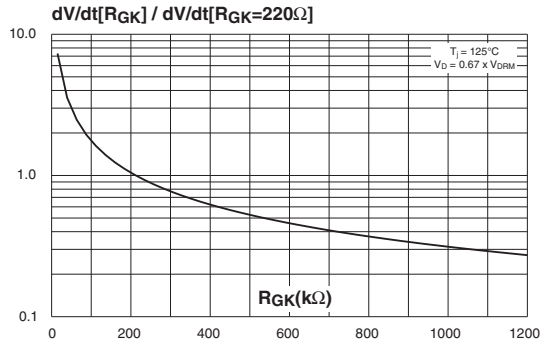


Figure 10: Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values) for TS8 series

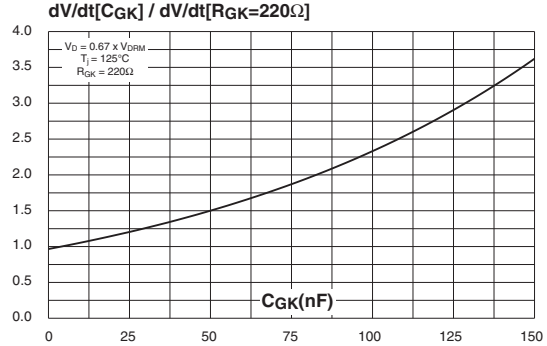


Figure 11: Surge peak on-state current versus number of cycles

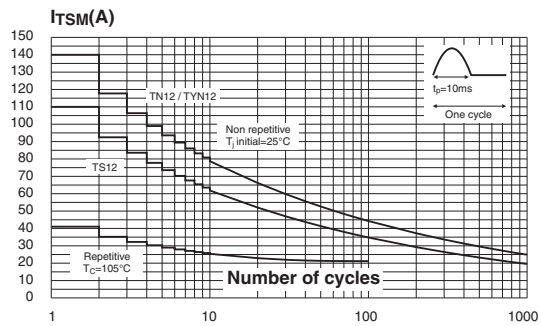


Figure 12: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ ms}$, and corresponding values of I^2t

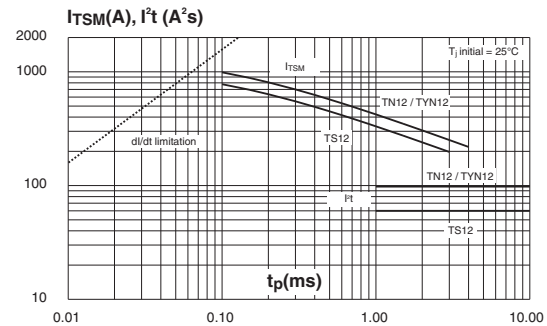


Figure 13: On-state characteristics (maximum values)

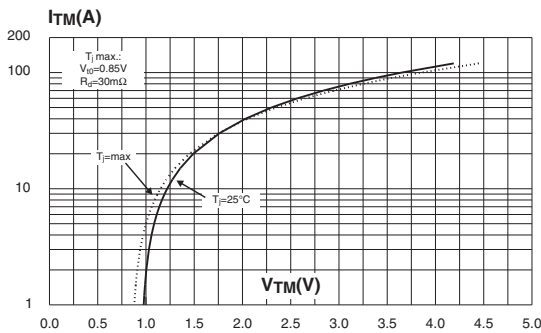
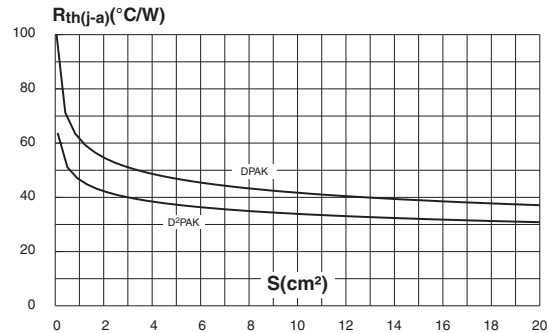


Figure 14: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board FR4, copper thickness: 35 μm) (DPAK and D²PAK)



TN12, TS12 and TYNx12 Series

Figure 15: Ordering Information Scheme (TN8 series)

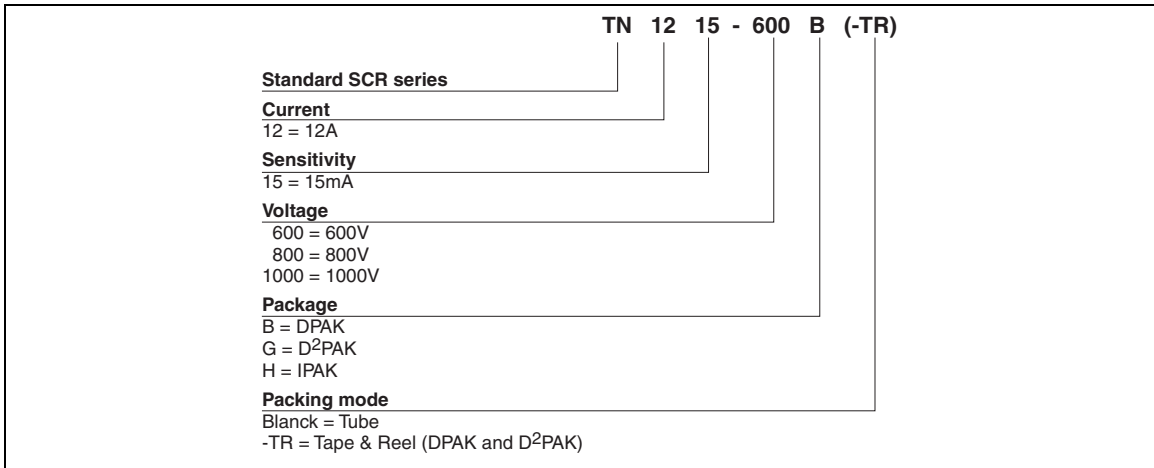


Figure 16: Ordering Information Scheme (TS8 series)

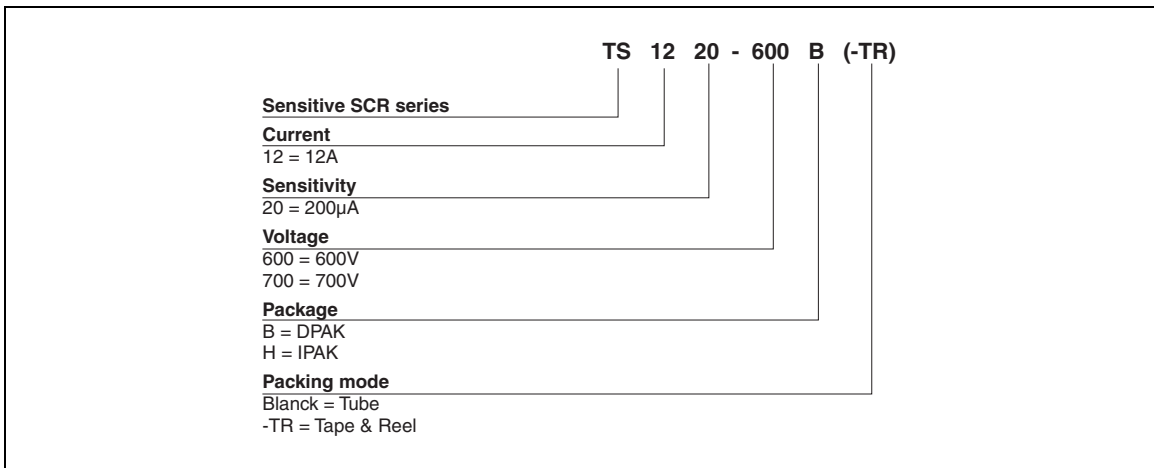


Figure 17: Ordering Information Scheme (TYN08 series)

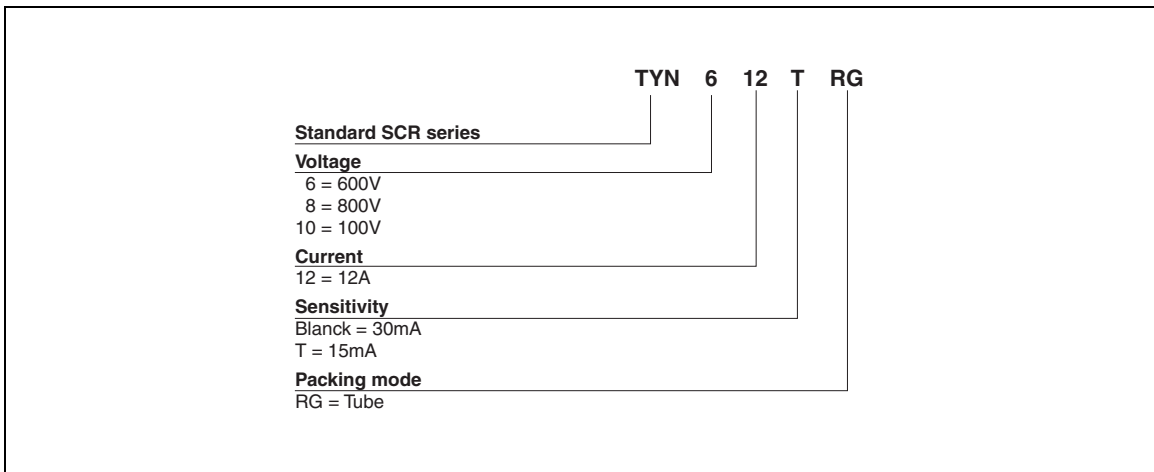


Table 7: Product Selector

| Part Numbers | Voltage (xxx) | | | | Sensitivity | Package |
|--------------|---------------|-------|-------|--------|-------------|--------------------|
| | 600 V | 700 V | 800 V | 1000 V | | |
| TN1215-xxxB | X | | X | | 15 mA | DPAK |
| TN1215-xxxG | X | | X | X | 15 mA | D ² PAK |
| TN1215-xxxH | X | | X | | 15 mA | IPAK |
| TS1220-xxxB | X | X | | | 0.2 mA | DPAK |
| TS1220-xxxH | X | X | | | 0.2 mA | IPAK |
| TYNx12 | X | | X | X | 15 mA | TO-220AB |
| TYNx12T | X | | X | X | 5 mA | TO-220AB |

Figure 18: DPAK Package Mechanical Data

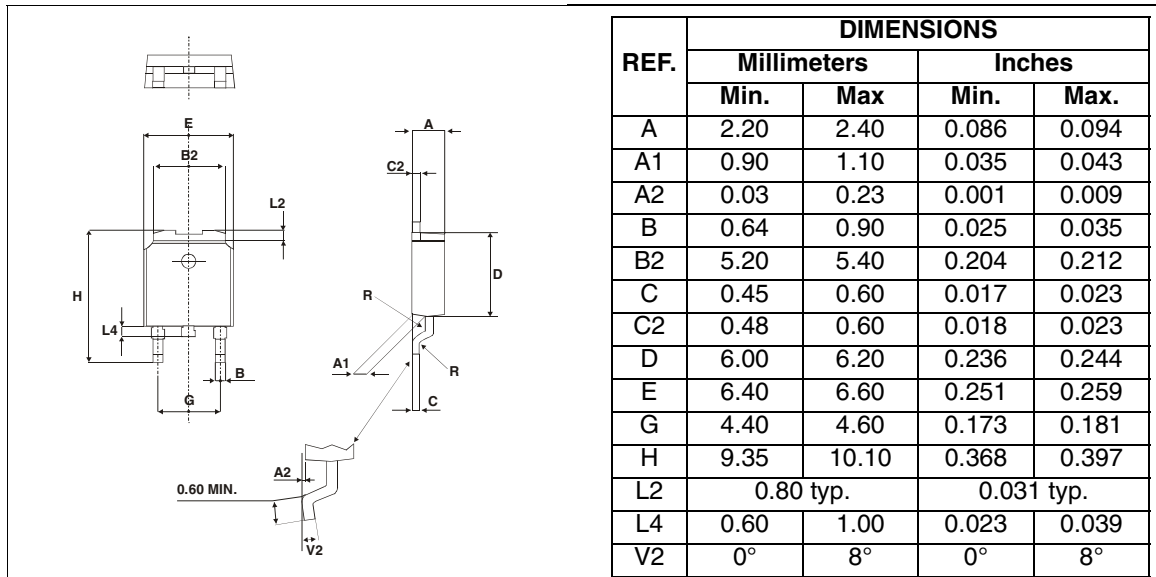


Figure 19: DPAK Foot Print Dimensions (in millimeters)

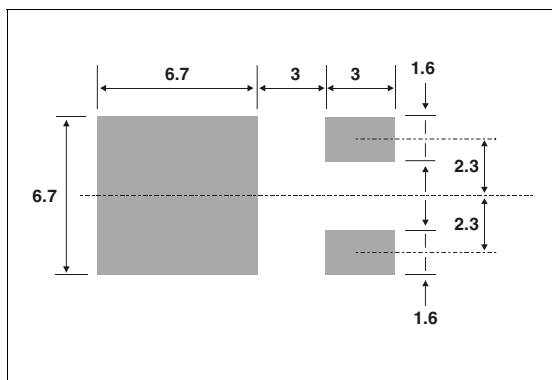


Figure 20: D²PAK Package Mechanical Data

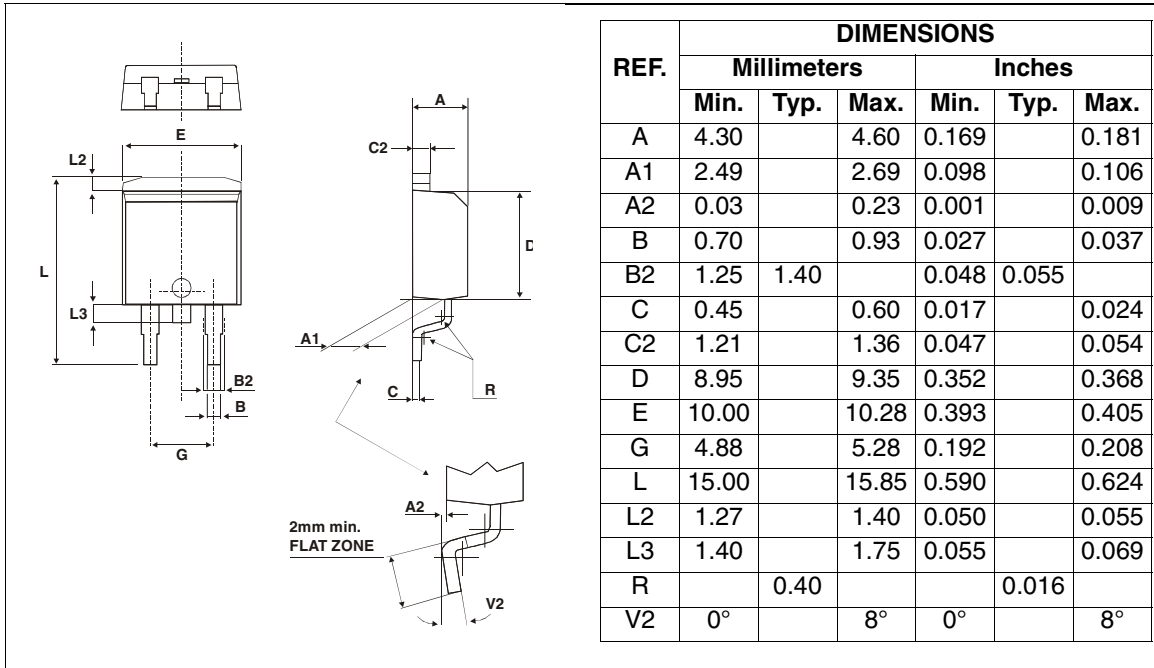


Figure 21: D²PAK Foot Print Dimensions
(in millimeters)

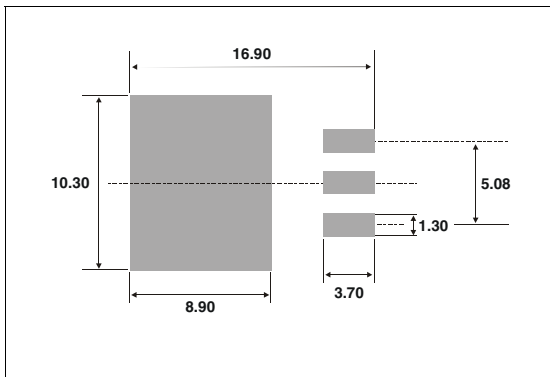


Figure 22: IPAK Package Mechanical Data

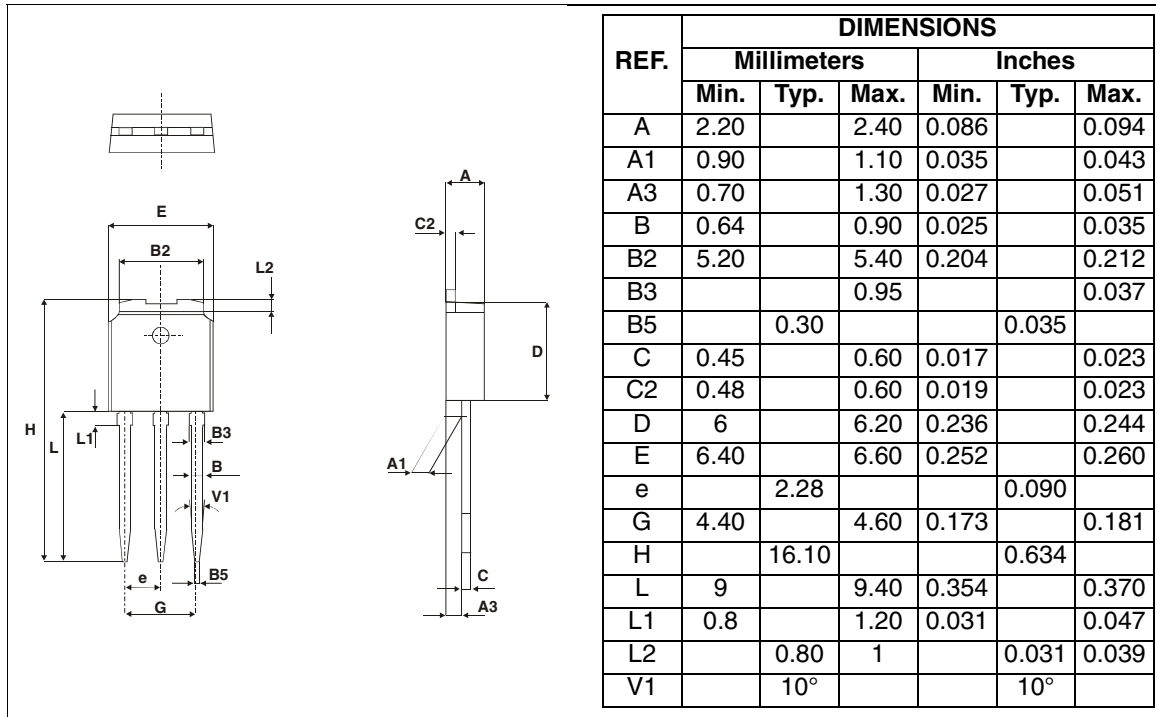
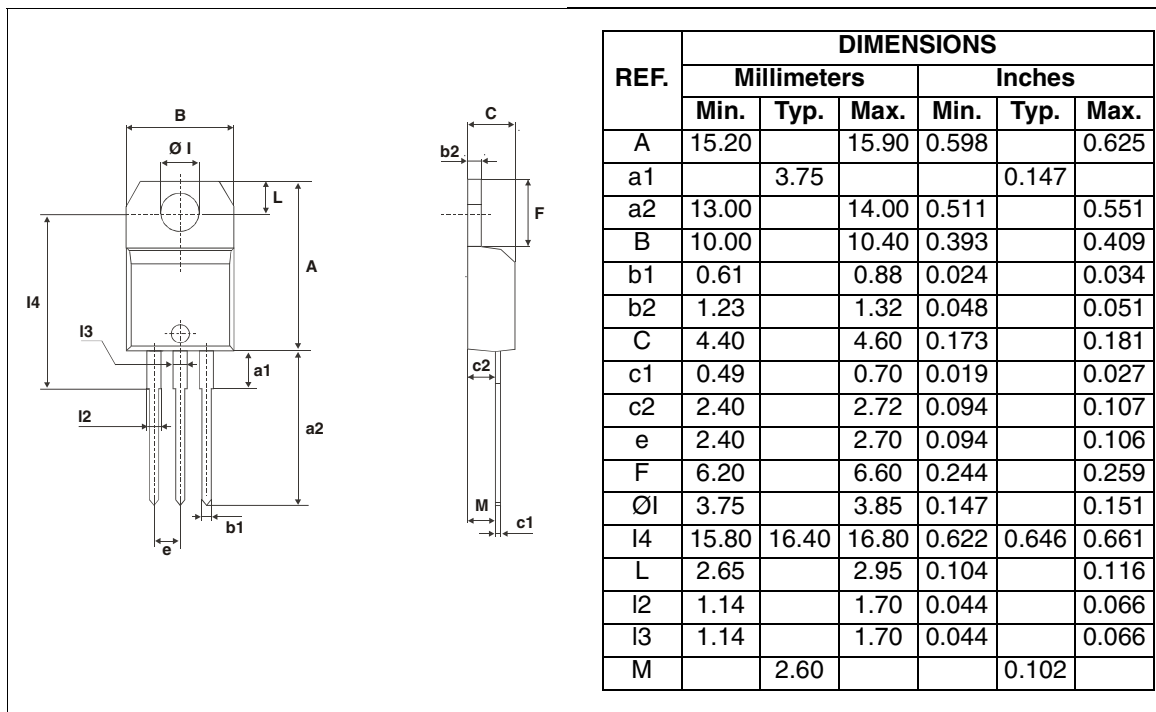


Figure 23: TO-220AB Package Mechanical Data



TN12, TS12 and TYNx12 Series

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8: Ordering Information

| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|----------------|------------|--------------------|--------|----------|---------------|
| TN1215-x00B | TN1215x00 | DPAK | 0.3 g | 75 | Tube |
| TN1215-x00B-TR | TN1215x00 | DPAK | 0.3 g | 2500 | Tape & reel |
| TN1215-x00G | TN1215x00G | D ² PAK | 1.5 g | 50 | Tube |
| TN1215-x00G-TR | TN1215x00G | D ² PAK | 1.5 g | 1000 | Tape & reel |
| TN1215-x00H | TN1215x00 | IPAK | 0.3 g | 75 | Tube |
| TS1220-x00B | TS1220x00 | DPAK | 0.3 g | 75 | Tube |
| TS1220-x00B-TR | TS1220x00 | DPAK | 0.3 g | 2500 | Tape & reel |
| TS1220-x00H | TS1220x00 | IPAK | 0.3 g | 75 | Tube |
| TYNx12RG | TYNx12 | TO-220AB | 2.3 g | 50 | Tube |
| TYNx12TRG | TYNx12T | TO-220AB | 2.3 g | 50 | Tube |

Note: x = voltage

Table 9: Revision History

| Date | Revision | Description of Changes |
|-------------|----------|---|
| Sep-2000 | 3 | Last update. |
| 25-Mar-2005 | 4 | TO-220AB delivery mode changed from bulk to tube. |
| 14-Oct-2005 | 5 | Changed sensitivity values in Table 7 for TYNx12 (30 to 15 mA) and TYNx12T (15 to 5 mA). Added ECOPACK statement |

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